

COLLEGE OF ENGINEERING PUTRAJAYA CAMPUS FINAL EXAMINATION

SEMESTER 1 2017 / 2018

PROGRAMME	: Bachelor of Electrical & Electronics Engineering (Honours) Bachelor of Electrical Power Engineering (Honours)
SUBJECT CODE	: EEEB273
SUBJECT	: ELECTRONIC ANALYSIS AND DESIGN II
DATE	: September 2017
TIME	: 3 hours

INSTRUCTIONS TO CANDIDATES:

- 1. This paper contains **FIVE** (5) questions in **NINE** (9) pages.
- 2. Answer **ALL** questions.
- 3. Write **all** answers in the answer booklet provided. **Use pen** to write your answer.
- 4. Write answer to different question on **a new page**.

THIS QUESTION PAPER CONSISTS OF NINE (9) PRINTED PAGES INCLUDING THIS COVER PAGE.

Question 1 [20 marks]

Figure 1 is NMOS current source circuit with the transistor M_2 sourcing a bias current to the load circuit.

- (a) Draw the **PMOS version** of the current source. [5 marks]
- (b) Using the PMOS current source circuit drawn in Question 1(a), assume that the circuit is biased at $V^+ = 5$ V and $V^- = -5$ V. The transistors parameters are $V_{TP} = -0.5$ V, $k'_p = 50 \ \mu \text{A/V}^2$, $(W/L)_1 = (W/L)_2 = 15$, $(W/L)_3 = 3$, and $\lambda = 0$. Calculate I_{REF} , I_O and $V_{SD2}(\text{sat})$. [15 marks]



Question 2 [20 marks]

For a **MOSFET differential amplifier** shown in **Figure 2** the circuit parameters are: $V^+ = 3$ V and $V^- = -3$ V. Transistor parameters for **N-MOSFET** are: $V_{TN} = 0.5$ V, $k'_n = 100 \ \mu A/V^2$ and λ_n = 0.02 V⁻¹; and the transistor parameters for **P-MOSFET** are: $V_{TP} = -0.5$ V, $k'_p = 40 \ \mu A/V^2$ and $\lambda_p = 0.03$ V⁻¹. The transistor aspect ratios are: $(W/L)_I = 20$, $(W/L)_2 = 80$ and for the other transistors, $(W/L)_{3-I0} = 10$. It is given that $I_{REF} = 0.5$ mA.

- (a) Calculate the differential gain A_d . [6 marks]
- (b) The biasing constant current source I_Q is a **cascode current source**. Calculate the **output** resistance, R_o of the current source. [4 marks]
- (c) It is given that the common-mode rejection ratio (CMRR) of the differential amplifier is **71dB**. By how much should the output resistance, R_o of the cascode current source should decrease or increase such that the **CMRR increases to 80dB**? Calculate the new value of the output resistance.

[10 marks]



Figure 2

Question 3 [20 marks]

The transistor parameters for the circuit in Figure 3 are: $\beta = 200$, $V_{BE}(on) = 0.7$ V, and $V_A = 80$ V. For Q_1 and Q_2 , $V_A = \infty$. The diff-amp has a common-mode voltage gain of $A_{cm1} = -0.0749$. It is given that $I_{C3} = 1.886$ mA and $I_{C5} = 1.003$ mA.

- (a) Calculate the differential-mode input resistance (R_{id}) and common-mode input resistance (R_{icm}) . [7 marks]
- (b) Determine the differential-mode voltage gain $A_d = v_{O3}/v_d$ and the common-mode voltage gain $A_{cm} = v_{O3}/v_{cm}$. [10 marks]
- (c) If $A_{cm} = 0$, determine the **output voltage** v_{O3} if $v_1 = 2.015 \sin \omega t \text{ mV}$ and $v_2 = 1.985 \sin \omega t \text{ mV}$. [3 marks]



Figure 3

Question 4 [25 marks]

- (a) Refer to the output stage circuits shown in **Figure 4(a)** and **Figure 4(b)**.
 - (i) Identify the output stage circuits shown in the Figure 4(a) and Figure 4(b). Then, describe clearly the differences between the output stages shown in the Figure 4(a) and Figure 4(b) in terms of advantage(s) and/or disadvantage(s) of the designs.

[5 marks]

(ii) For the output stage shown in Figure 4(b), assume that $V_{CC} = 10$ V, $V_{BB} = 1.35$ V, and $R_L = 1$ k Ω . Transistor Q_n and Q_p have $I_S = 4 \times 10^{-15}$ A. Given that output voltage $v_0 = -8$ V, calculate the currents i_L, i_{Cn} , and i_{Cp} , the input voltage v_I , and the power dissipation in the transistors Q_n and Q_p . [10 marks]



Figure 4(a)

Figure 4(b)

(b) The 741 op-amp is shown in **Figure 5.** The minimum recommended supply voltages are $V^+ = 5$ V and $V^- = -5$ V. Assume that $V_{BE(on)} = V_{EB(on)} = 0.65$ V, $\beta_n = 200$, and $\beta_p = 60$. Calculate I_{C16} if $R_8 = 0$. What is the function of resistor R_8 in the gain stage?

[10 marks]



Figure 5

Question 5 [15 marks]

(a) Consider two (2) ideal op-amp circuits connected in cascade as shown in Figure 6. Given that $R_1 = 50 \text{ k}\Omega$, $R_2 = 100 \text{ k}\Omega$, $R_3 = 80 \text{ k}\Omega$, and $R_4 = 75 \text{ k}\Omega$. Calculate voltage gain v_O/v_I of the overall circuit. [5 marks]



Figure 6

(b) Figure 7 in the following page shows a design for an instrumentation amplifier using op-amps. The instrumentation amplifier has adjustable differential voltage gain (A_v) . In the design, R_{1POT} is a potentiometer (or a variable resistor) used to provide variable resistance so that differential voltage gain of the instrumentation amplifier can be adjustable. With analysis, it can be shown that output voltage (v_0) for the difference amplifier constructed using op-amp A_3 , resistors R_3 , and resistors R_4 is

$$v_{O} = \frac{R_4}{R_3} \left(v_{O2} - v_{O1} \right)$$

(i) Study Figure 7 carefully. Using same labels for all resistors, voltages and currents given in the Figure 7, show that the output voltage (v_0) of the instrumentation amplifier with adjustable differential voltage gain is

[7 marks]

$$v_{O} = \frac{R_{4}}{R_{3}} \left(1 + \frac{2R_{2}}{R_{1f} + R_{1POT}} \right) (v_{I2} - v_{I1})$$

(ii) For the circuit in Figure 7, given that $R_4 = 2.5 R_3$, $R_2 = 495 k\Omega$, $R_{1f} = 15 k\Omega$, R_{1POT} is set at 40 k Ω , $v_{I1} = 0.090$ V, and $v_{I2} = 0.115$ V. Calculate adjustable differential voltage gain (A_v) and the output voltage (v_0) of the circuit.

[3 marks]



Figure 7

-END OF QUESTION PAPER-

APPENDIX:

A) BASIC FORMULA FOR TRANSISTOR

BJTMOSFET
$$i_C = I_S e^{v_{BE}/V_T}$$
; NPN; N - MOSFET $i_C = I_S e^{v_{EB}/V_T}$; PNP $v_{DS} (sat) = v_{GS} - V_T$ $i_C = \beta i_B = \frac{\beta}{\beta + 1} i_E$ $i_D = K_n [v_{GS} - V_{TN}]$ $i_E = i_B + i_C$ $K_n = \frac{\mu_n C_{ox} W}{2L} = \frac{k}{2}$;Small signal $v_{SD} (sat) = v_{SG} + V_T$ $\beta = g_m r_{\pi}$ $i_D = K_p [v_{SG} + V_{TP}]$ $g_m = \frac{I_{CQ}}{V_T}$ $K_p = \frac{\mu_p C_{ox} W}{2L} = \frac{k}{2}$ $r_{\pi} = \frac{\beta V_T}{I_{CQ}}$ $g_m = 2\sqrt{K_n I_{DQ}}$; $r_o = \frac{V_A}{I_{CQ}}$ 1

$$r_o = \frac{V_A}{I_{CQ}}$$
$$V_T = 26 \text{ mV}$$

ΓN 2 $\frac{k_n}{2} \cdot \frac{W}{L}$ ΓP 2 $\frac{k_p}{2} \cdot \frac{W}{L}$ N-MOSFET ; P-MOSFET $r_o \cong \frac{1}{\lambda I_{DQ}}$

B) <u>HYBRID-π EQUIVALENT CIRCUITS</u>





C) QUADRATIC FORMULA

$$Ax^{2} + Bx + C = 0 \qquad \rightarrow \quad x = \frac{-B \pm \sqrt{B^{2} - 4AC}}{2A}$$